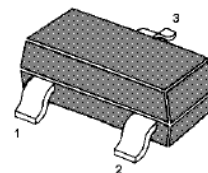
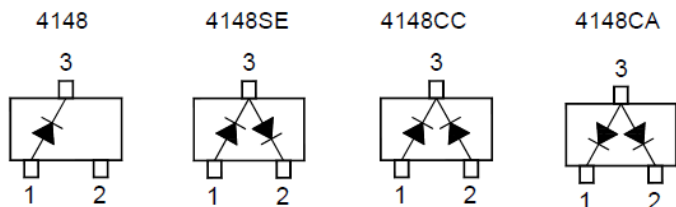


Kingtronics®**MMBD4148**Silicon Epitaxial Planar
Switching Diode

MMBD4148 Marking Code: **5D**
 MMBD4148SE Marking Code: **A7**
 MMBD4148CC Marking Code: **A4**
 MMBD4148CA Marking Code: **A1**
 TO-236 Plastic Package

Absolute Maximum Ratings (Ta = 25°C)

PARAMETER	SYMBOL	VALUE	UNIT
Maximum Repetitive Reverse Voltage	VRRM	100	V
Reverse Voltage	VR	75	V
Average Rectified Forward Current	IF(AV)	200	mA
DC Forward Current	IFM	600	mA
Recurrent Peak Forward Current	IFRM	700	mA
Non-repetitive Peak Forward Surge Current at t = 1 s	IFSM	1	A
at t = 1 μs		2	
Total Device Dissipation	P _{tot}	350	mW
Operating Junction Temperature	T _j	150	°C
Storage Temperature Range	Tstg	- 55 to + 150	°C

Electrical Characteristics (Ta = 25°C)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT
Forward Voltage at I _F = 10 mA	V _F	-	1	V
Reverse Breakdown Voltage at I _R = 100 μA	V _{(BR)R}	100	-	V
at I _R = 5 μA		75	-	
Reverse Current at V _R = 20 V	I _R	-	25	nA
at V _R = 75 V		-	5	μA
at V _R = 20 V, Ta = 150 °C		-	50	μA
Reverse Recovery Time at I _F = 10 mA, V _R = 6 V, I _{RR} = 1 mA, R _L = 100 Ω	t _{rr}	-	4	ns
Total Capacitance at V _R = 0 V, f = 1 MHz	C _T	-	4	pF

Kingtronics® International Company

Website: www.kingtronics.com Email: info@kingtronics.com Tel: (852) 8106 7033 Fax: (852) 8106 7099

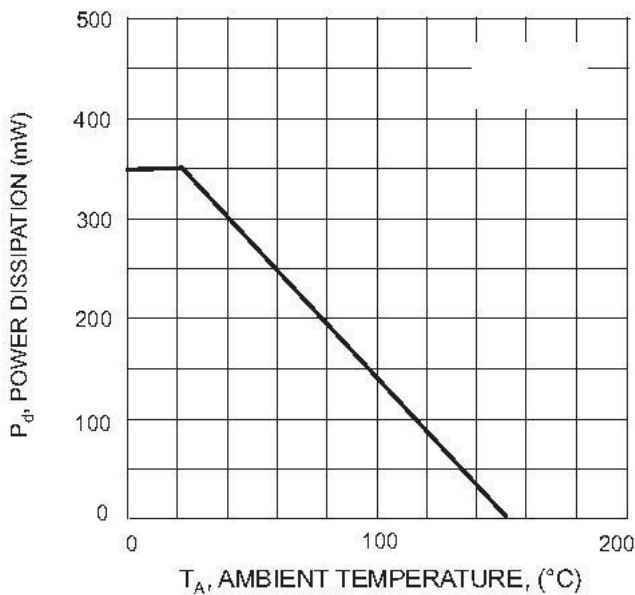


Fig. 1 Power Derating Curve

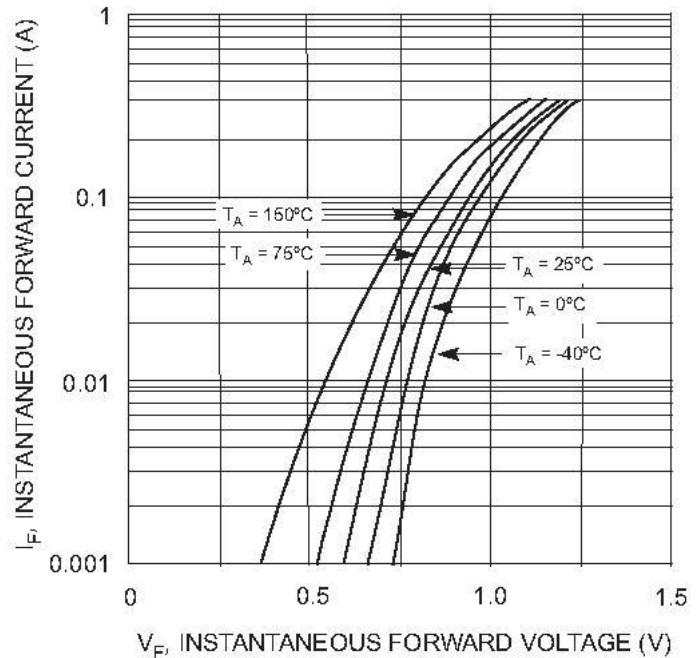


Fig. 2 Forward Characteristics

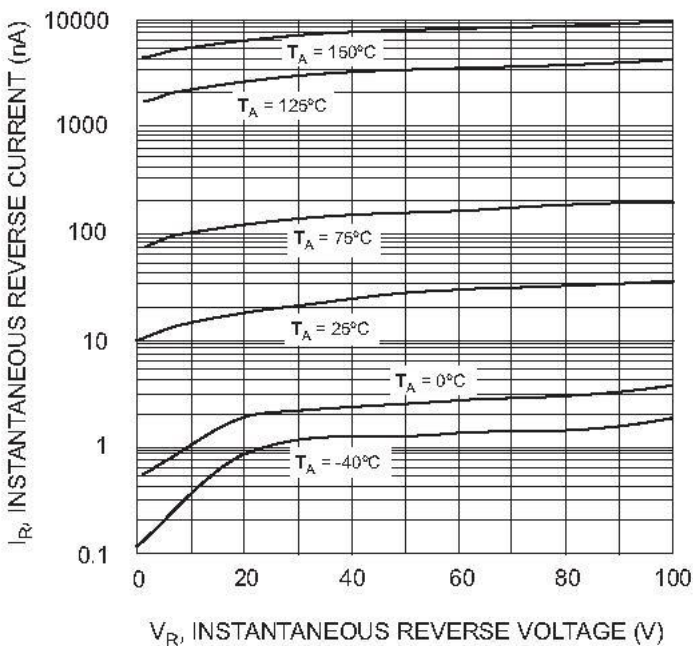


Fig. 3 Typical Reverse Characteristics

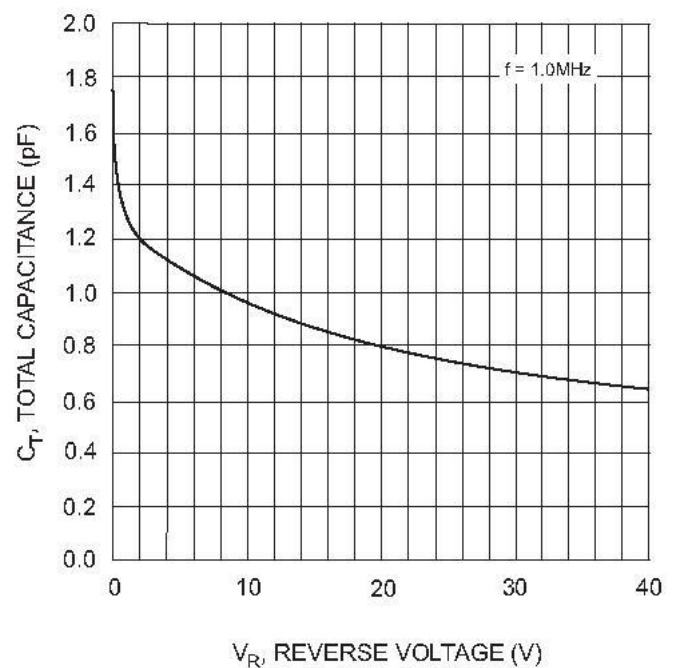


Fig. 4 Typical Capacitance vs. Reverse Voltage

Note: Specifications are subject to change without notice